DOCKET NO. 00-654

In the Specification:

Please replace the paragraph beginning at page 1, line 6, with the following rewritten paragraph:

---The subject matter of this application relates to the subject matter of U.S. Patent No. 6,350,700, issued February 26, 2002, entitled "PROCESS FOR FORMING TRENCHES AND VIAS IN LAYERS OF LOW DIELECTRIC CONSTANT CARBON-DOPED SILICON OXIDE DIELECTRIC MATERIAL OF AN INTEGRATED CIRCUIT STRUCTURE WHILE INHIBITING DAMAGE TO THE LAYERS OF LOW DIELECTRIC CONSTANT CARBON-DOPED SILICON OXIDE DIELECTRIC MATERIAL", assigned to the assignee of this application, and the subject matter of which is hereby incorporated herein by reference.--

Please replace the paragraph beginning at page 1, line 13, with the following rewritten paragraph:

---The subject matter of this application relates to the subject matter of U.S. Patent No. 6,368,979, issued April 9, 2002, entitled "PROCESS FOR FORMING TRENCHES AND VIAS IN LAYERS OF LOW DIELECTRIC CONSTANT CARBON-DOPED SILICON OXIDE DIELECTRIC MATERIAL OF AN INTEGRATED CIRCUIT STRUCTURE", assigned to the assignee of this application, and the subject matter of which is hereby incorporated herein by reference.--

Please replace the paragraph beginning at page 8, line 17, with the following rewritten paragraph:

--The layers of low k dielectric material described herein may comprise carbon-doped silicon oxide dielectric material or any other type of low k dielectric material capable of being treated in a plasma to form, from the surface portion of the low k dielectric layer, a densified layer of dielectric material having characteristics resembling a conventional (non-low k) silicon oxide or silicon carbide dielectric material. Low k dielectric material suitable for use in this invention and capable of being treated to form the desired layer or layers of densified dielectric material can be formed using processes and equipment commercially available from, for example, Novellus, AMAT, Trikon, ASM, Dow Corning, Hitachi, Dow Chemical, Honeywell, Schumacher, and W.L. Gore. Other low k dielectric materials which may be used in the process of the invention include the low k dielectric materials described in U.S. Patent No. 6,303,047, issued October 16, 2001, and U.S. Patent Application Serial Nos. 09/590,310; 09/792,683; 09/792,685; and 09/792,691; all assigned to the assignee of the invention; and the subject matter of each of which is hereby incorporated by reference. The formation of densified dielectric material on the surface of a low k dielectric material is also disclosed in Sukharev et al. U.S. Patent No. 6,114,259, issued September 5, 2000 and assigned to the assignee of this application, and the subject matter of which is hereby incorporated herein by reference.--